

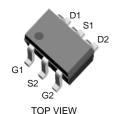
#### **DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

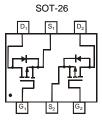
#### **Features**

- Dual P-Channel MOSFET
- Low On-Resistance
  - 150 m $\Omega$  @ V<sub>GS</sub> = -4.5V
  - 200 m $\Omega$  @ V<sub>GS</sub> = -2.5V
  - 240 mΩ @ V<sub>GS</sub> = -1.8V
- Very Low Gate Threshold Voltage V<sub>GS(th)</sub> ≤ 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

## **Mechanical Data**

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208
- · Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.015 grams (approximate)





TOP VIEW Internal Schematic

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		$V_{DSS}$	-20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 1)	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	-2.0 -1.5	А
Pulsed Drain Current		I <sub>DM</sub>	-7	Α

## **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P <sub>D</sub>	600	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	208	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB.
- 2. No purposefully added lead.
- No purposeruny added read.
   Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

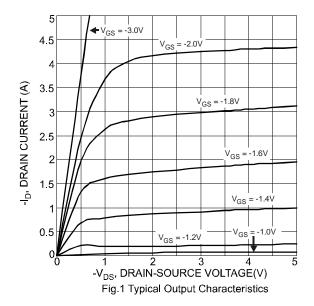


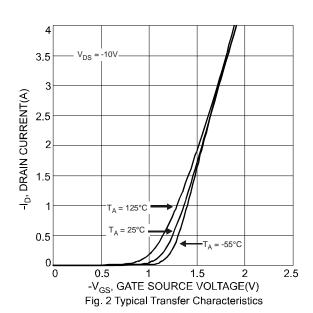
## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)								
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	-20			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	$T_J = 25$ °C $T_J = 125$ °C	I <sub>DSS</sub>	_		-1.0 -5.0	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage		I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)								
Gate Threshold Voltage		$V_{GS(th)}$	-0.45	_	-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance		R <sub>DS (ON)</sub>	_	92 134 180	150 200 240	mΩ	$V_{GS} = -4.5V, I_D = -2.0A$ $V_{GS} = -2.5V, I_D = -1.5A$ $V_{GS} = -1.8V, I_D = -0.5A$	
Forward Transconductance		<b>g</b> FS	_	3.1		S	$V_{DS} = -10V, I_{D} = -810mA$	
Diode Forward Voltage (Note 4)		$V_{SD}$	_	_	-0.9	V	$V_{GS} = 0V, I_S = -0.5A$	
DYNAMIC CHARACTERISTICS								
Input Capacitance		C <sub>iss</sub>	_	320		pF	10/1/	
Output Capacitance		Coss	_	80		рF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	60		pF	1 = 1.000112		
Turn-On Delay Time		t <sub>D(on)</sub>	_	11.51		ns		
Turn-On Rise Time	t <sub>r</sub>	_	12.09		ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	55.34	_	ns	$R_G = 6\Omega$ , $R_L = 10\Omega$		
Turn-Off Fall Time		t <sub>f</sub>	_	27.54	_	ns		

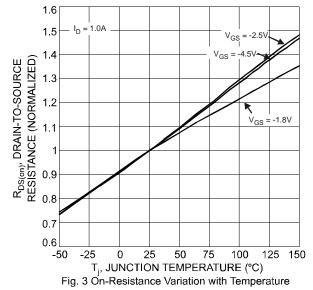
Notes:

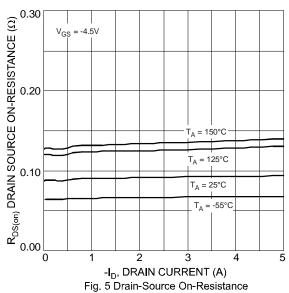
4. Short duration pulse test used to minimize self-heating effect.

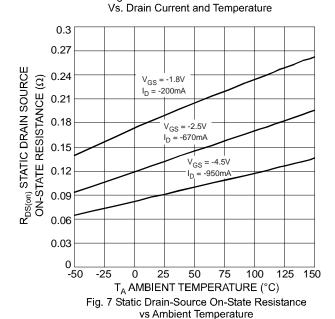












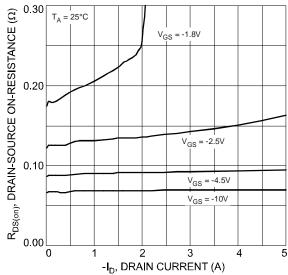
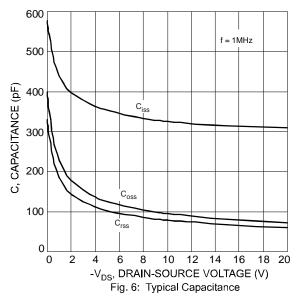
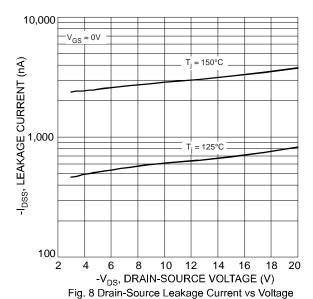
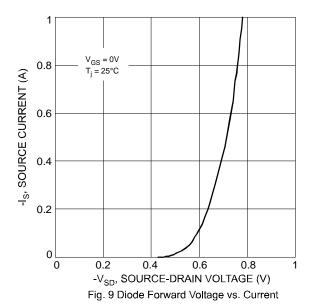


Fig. 4 On-Resistance vs Drain Current and Gate Voltage







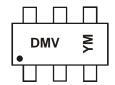


## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2240UDM-7	SOT-26	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**

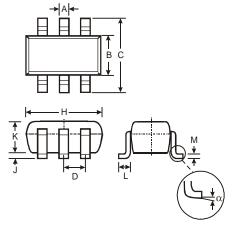


DMV = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	l	J	\	/	V	V	)	<	`	1	Z	7_
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

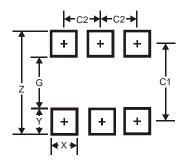
## **Package Outline Dimensions**



	SOT-26					
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	<u> </u>					
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	<b>K</b> 1.00 1.30 1.10					
L	L 0.35 0.55 0.40					
M	0.10	0.20	0.15			
α	0°	8°	_			
All Dimensions in mm						



## Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95

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